Atomic Layer Deposition Applications 4

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Table of Contents

Preface *iii*

Chapter 1
Emerging ALD Applications I

Deposition of Organic- Inorganic Hybrid Materials by Atomic Layer Deposition * 3
O. Nilsen, K. Klepper, H. Nielsen and H. Fjellvåg

Opportunities of ALD for Thin Film Solid Oxide Fuel Cells * 15
F. Prinz

Leading Edge Atomic Layer Deposition Applications * 19
G. Sundaram, D. Monsma and J. Becker

Fabrication and Characterization of Lead Sulfide Thin Films by Atomic Layer Deposition 29
N. P. Dasgupta, S. P. Walch and F. Prinz

Chapter 2
High-k Gate Devices

Comparison of Gate Sensitivity for Spin Interference Effect between Al_2O_3 and SiO_2 Gate Insulators on InGaAs Based Mesoscopic Ring Arrays * 39
M. Kohda, J. Takagi and J. Nitta

Electrical Properties of High-k ALD HfO2 Deposited on Strained Si Layers Epitaxially Grown on Si0.8Ge0.2/Si Substrates 51
P. R. Shrestha, D. Gu, K. Tapily and H. Baumgart

Fabrication of Self-aligned Enhancement-mode n-channel GaAs MOSFETs Employing a Wet Clean Process for GaAs Substrates 59
D. Shahrjerdi, D. Garcia-Guteirrez, S. Kim, M. M. Hasan, K. Varahramyan, E. Tutuc and S. Banerjee

Application of Advanced Atomic Layer Deposition for Understanding and Control of VTH and EOT in Metal/High-k Gate Stacks * 69
A. Toriumi, T. Nabatame and H. Ota

Chapter 3
ALD Precursor Development

Design and Development of ALD Precursors for Microelectronics * 79
R. K. Kanjolia, J. Anthis, R. Odedra, P. Williams and P. N. Heys

Novel Zirconium Precursors for Atomic Layer Deposition of ZrO2 films 87
T. Chen, T. M. Cameron, S. D. Nguyen, G. T. Stauf, D. W. Peters, L. Maylott, W. Li, C. Xu, J. F. Roeder, B. C. Hendrix, M. Hilgarth, J. Niinisto, K. Kukli, M. Ritala and M. Leskela

Development of ALD Precursors for Semiconductor Devices * 103
S. Wada, T. Abe, A. Sakurai, T. Higashino, R. Fujimoto and M. Shimizu

Ti Source Precursors for Atomic Layer Deposition of TiO2, STO and BST 113
R. Katamreddy, V. Omarjee, B. Feist and C. Dussarrat

Chapter 4
Progress in ALD Equipment for Advanced Applications

Advances in ALD Equipment for sub-40nm Memory Capacitor Dielectrics: Precursor delivery, Materials and Processes * 125
Z. Karim, Y. Senzaki, S. Ramanathan, J. Lindner, H. Silva and M. Dauelsberg

Batch Atomic Layer Deposition of HfO2 and ZrO2 Films Using Cyclopentadienyl Precursors 135
P. R. Fischer, D. Pierreux, O. Rouault, J. Sirugue, P. M. Zagwijn, E. Tois and S. Haukka

Chapter 5
Emerging ALD Applications II

Atomic Layer Deposition as a Synthesis Method for Inorganic Membranes * 151
D. Cassidy, S. Higgins, B. A. McCool and W. J. DeSisto

Synthesis of Zirconia and Hafnia Tubes by Atomic Layer Deposition (ALD) Template Method 159
T. M. Abdel-Fattah, D. Gu, H. Baumgart and G. Namkoong

Controlled Synthesis of 3D Nanostructures Using Proximity-Field Nanopatterning Lithography and Graded Temperature ALD * 165
R. K. Grubbs, A. R. Ellis, A. M. Sanchez, M. Wiwi, I. El-kady, K. Bogart, M. F. Su, C. Christodoulou, M. Taha, D. L. Shir and J. Rogers

Oxidative Removal of Self-Assembled Monolayers for Selective Atomic Layer Deposition 173
W. Lee, C. Chao, X. Jiang, J. Hwang, S. Bent and F. Prinz

Formation of Metal-Semiconductor Core-shell Nanoparticles Using Electrochemical Atomic Layer Deposition 181
C. Gu, H. Xu, M. Park and C. Shannon

Chapter 6
ALD of Metal Films

PEALD Ru Liner Conformality and Cu Trench Fill Characteristics * 193
O. van der Straten, J. Wynne, T. Vo, J. Maniscalco, T. Nogami, I. Ali, S. Chiang, J. Ren and P. Ma

Morphology of Electrodeposited Cu on 300 mm PEALD Ru Substrates 201
J. Kelly, T. Vo, O. van der Straten, Q. Huang, B. Baker O'Neal, X. I. Shao, S. Chiang and J. Dukovic

Remote Plasma and Thermal ALD of Platinum and Platinum Oxide Films 209
H. C. Knoops, A. Mackus, M. Donders, M. C. van de Sanden, P. Notten and W. M. Kessels

Area Selective Atomic Layer Deposition of Cobalt Thin Films 219
H. Lee and H. Kim

Characteristics of Tantalum Carbo-nitride Thin Films Deposited with Atomic Layer Deposition Process 227
M. Song and S. Rhee

Chapter 7
ALD Processing and Characterization

Thermal Versus Plasma-Enhanced ALD: Growth Kinetics and Conformality * 239
C. Detavernier, J. Dendooven, D. Deduytsche and J. Musschoot

Plasma-Assisted ALD of Al2O3 at Low Temperatures: Reaction Mechanisms and Material Properties 247
E. Langereis, M. Bouman, J. Keijmel, S. Heil, M. C. van de Sanden and W. M. Kessels

HfO2 Atomic Layer Deposition Using HfCl4/H2O: The First Reaction Cycle * 257
L. Nyns, A. Delabie, M. Caymax, M. Heyns, S. Van Elshocht, C. Vinckier and S. De Gendt

Comparison of Nanomechanical Behavior of the Amorphous and Crystalline Phases of ALD HfO2 269
K. Tapily, J. Jakes, P. R. Shrestha, D. Gu, H. Baumgart and A. Elmustafa

Carboxylic Acids as Oxygen Supplying Agents for Atomic Layer Deposition of High-k Thin Films 279
E. Rauwel, F. Ducroquet, P. Rauwel, M. Willinger, I. Matko, D. Kiselev and N. Pinna

High-K Gate Dielectric Structures by Atomic Layer Deposition for the 32nm and Beyond Nodes * 291
R. D. Clark, S. Consiglio, C. Wajda, G. Leusink, T. Sugawara, H. Nakabayashi, H. Jagannathan, L. F. Edge, P. Jamison, V. Paruchuri, R. Iijima, M. Takayanagi, B. Linder, J. Bruley, M. Copel and V. Narayanan

Chapter 8
Poster Session

Two Step Annealing of Iridium Thin Films prepared by Plasma-Enhanced Atomic Layer Deposition 309
S. Kim, S. Kwon and S. Kang

Atomic Layer Deposited IrO2-TiO2 Thin Film Resistor for the Thermal Inkjet Printheads 315
S. Kwon, S. Kim, S. Jeong, K. Kim and S. Kang

Enhanced Band Gap and Defect Structure of Low Dielectric Photonic Crystals Using ALD Coatings 321
M. Thitsa and S. Albin

Photoluminescence of GaQ3-Al2O3 Core-Shell Nanowires 329
C. Wang, C. Kei, Y. Tao and T. Perng

Characteristics of TiSiO Films for Varistors 337
J. Lim, S. Yun and H. Kim

Effects of Film Thickness and Preferred Orientation on the Dieletric Constants of Hf-Aluminate Films Deposited by PEALD 343
H. Moon, D. Joo, P. Park and S. Kang

In-Situ Probing of Atomic Layer Deposition Processes using Infrared and Near Infrared Spectroscopy 349
A. O'Mahony, I. M. Povey and M. E. Pemble

Atomic Vapor Deposited Tantalum Carbo-Nitride Film using TBTDET and Hydrogen 355
S. Kim, M. Song and S. Rhee

Author Index 363

** invited paper*